RoHS

COMPLIANT

HALOGEN

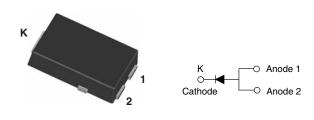
FREE



TO-277A (SMPC)

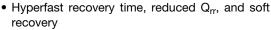
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Hyperfast Rectifier, 6 A FRED Pt®



PRODUCT SUMMARY				
Package	TO-277A (SMPC)			
I _{F(AV)}	6 A			
V _R	200 V			
V _F at I _F	0.74 V			
t _{rr (typ.)}	28 ns			
T _J max.	175 °C			
Diode variation	Single die			

FEATURES







Low forward voltage drop

· Low leakage current

 Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

• Meets JESD 201 class 2 whisker test

 Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V_{RRM}		200	V		
Average rectified forward current	I _{F(AV)}	T _{Sp} = 160 °C	6	۸		
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	150	Α		
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	L TEST CONDITIONS MIN.		TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	ı	-		
Forward voltage V _F	V	I _F = 6 A	-	0.87	0.94	V	
	I _F = 6 A, T _J = 125 °C	-	0.74	0.8			
Reverse leakage current I _R	V _R = V _R rated	-	-	2			
	'R	T _J = 125 °C, V _R = V _R rated	-	3	15	- μΑ	
Junction capacitance	C _T	V _R = 200 V	-	33	-	pF	



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A, } dI_F/dt = 50 \text{ A/}\mu\text{s, } V_R = 30 \text{ V}$		-	28	-	
Reverse recovery time t _{rr}	+	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	-	25	
	L _{rr}	T _J = 25 °C		-	22	-	ns
		T _J = 125 °C		-	33	-	
Peak recovery current I _{RRM}		T _J = 25 °C	I _F = 6 A	-	2.4	-	^
	T _J = 125 °C	dI _F /dt = 200 A/μs V _R = 160 V	-	5.0	-	Α	
Reverse recovery charge Q _{rr}	0	T _J = 25 °C		-	27	-	nC
	Q _{rr}	T _J = 125 °C		-	80	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to solder pad	R _{thJ-Sp}		-	2.2	3	°C/W
Approximate weight				0.1		g
Approximate weight				0.0035		OZ.
Marking device		Case style TO-277A (SMPC)		NE	H2	

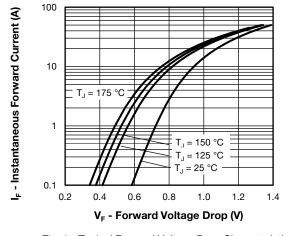


Fig. 1 - Typical Forward Voltage Drop Characteristics

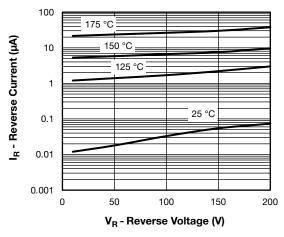


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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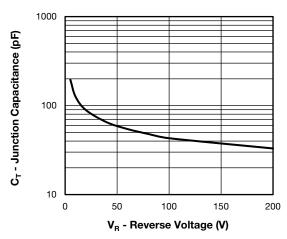


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

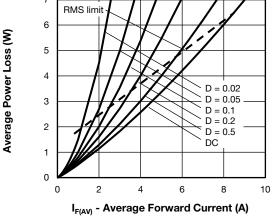


Fig. 5 - Forward Power Loss Characteristics

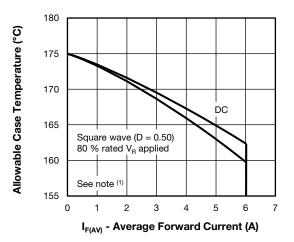


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

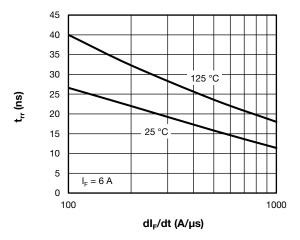


Fig. 6 - Typical Reverse Recovery Time vs. dl_F/dt

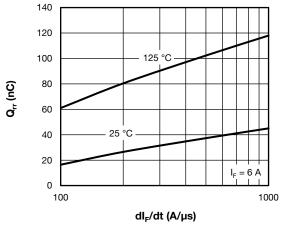


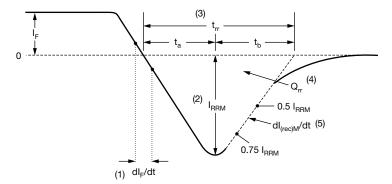
Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{ll} \text{(1)} \ \ \text{Formula used:} \ T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \ \text{at} \ (I_{F(AV)}/D) \ \text{(see fig. 5)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \ \text{(1 - D)}; \ I_R \ \text{at} \ V_{R1} = \text{rated} \ V_R \\ \end{array}$



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- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

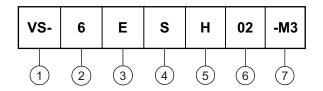
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- **2** Current rating (6 = 6 A)
- 3 Circuit configuration:

E = single diode

4 - S = SMPC package

5 - Process type,

H = hyperfast recovery

6 - Voltage code (02 = 200 V)

7 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-6ESH02-M3/86A	1500	1500	7" diameter plastic tape and reel		
VS-6ESH02-M3/87A	6500	6500	13" diameter plastic tape and reel		

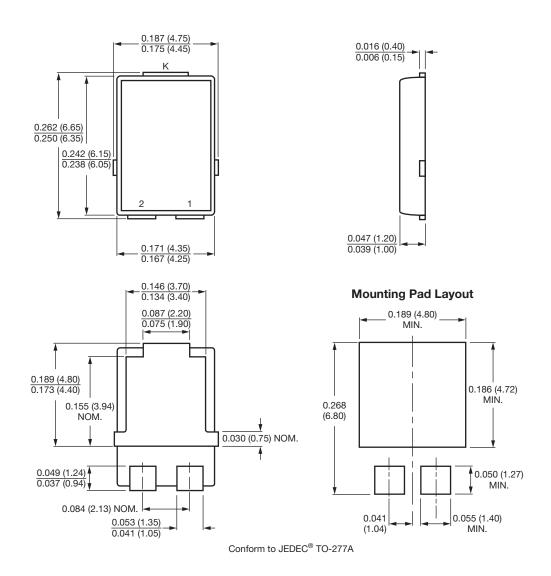
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95570			
Part marking information	www.vishay.com/doc?95565			
Packaging information	www.vishay.com/doc?88869			



Vishay Semiconductors

TO-277A (SMPC)

DIMENSIONS in inches (millimeters)





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Revision: 13-Jun-16 1 Document Number: 91000